

MOSFET – N-Channel, QFET

800 V, 12.6 A, 750 mΩ

FQA13N80-F109

Description

This N-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 12.6 A, 800 V, $R_{DS(on)} = 750\text{ m}\Omega$ (Max.) @ $V_{GS} = 10\text{ V}$, $I_D = 6.3\text{ A}$
- Low Gate Charge (Typ. 68 nC)
- Low C_{rss} (Typ. 30 pF)
- 100% Avalanche Tested
- This is Pb-Free and Halide Free Device

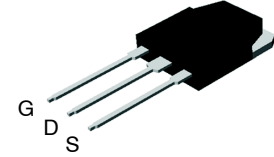
ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	800	V
I_D	Drain Current	-Continuous ($T_C = 25^\circ\text{C}$)	12.6
		-Continuous ($T_C = 100^\circ\text{C}$)	8.0
I_{DM}	Drain Current -Pulsed (Note 1)	50.4	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1100	mJ
I_{AR}	Avalanche Current (Note 1)	12.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	30	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	300
		-Derate Above 25°C	2.38
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from Case for 5 seconds	300	$^\circ\text{C}$

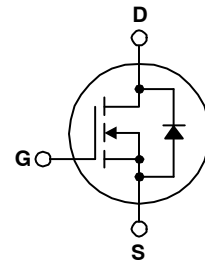
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $L = 13\text{ mH}$, $I_{AS} = 12.6\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 12.6\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.

V_{DSS}	$R_{DS(on)}$ MAX	I_D MAX
800 V	750 mΩ @ 10 V	12.6 A

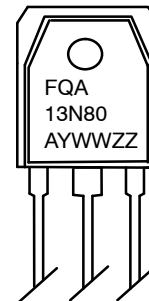


TO-3P-3LD
CASE 340BZ



N-CHANNEL MOSFET

MARKING DIAGRAM



FQA13N80 = Specific Device Code
A = Assembly Location
YWW = Date Code (Year & Week)
ZZ = Assembly Lot

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

FQA13N80-F109

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	800	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	0.95	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	10	μA
		$V_{DS} = 640 \text{ V}$, $T_C = 125^\circ\text{C}$	-	-	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	-100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 6.3 \text{ A}$	-	0.58	0.75	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}$, $I_D = 6.3 \text{ A}$	-	13	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	2700	3500	pF
C_{oss}	Output Capacitance		-	275	360	pF
C_{rss}	Reverse Transfer Capacitance		-	30	39	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400 \text{ V}$, $I_D = 12.6 \text{ A}$, $R_G = 25 \Omega$ (Note 4)	-	60	130	ns
t_r	Turn-On Rise Time		-	150	310	ns
$t_{d(off)}$	Turn-Off Delay Time		-	155	320	ns
t_f	Turn-Off Fall Time		-	110	230	ns
Q_g	Total Gate Charge	$V_{DS} = 640 \text{ V}$, $I_D = 12.6 \text{ A}$, $V_{GS} = 10 \text{ V}$ (Note 4)	-	68	88	nC
Q_{gs}	Gate-Source Charge		-	15	-	nC
Q_{gd}	Gate-Drain Charge		-	32	-	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Maximum Continuous Drain-Source Diode Forward Current	-	-	12.6	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	-	-	50.4	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 12.6 \text{ A}$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $I_S = 12.6 \text{ A}$, $di_F/dt = 100 \text{ A}/\mu\text{s}$	-	850	-	ns
Q_{rr}	Reverse Recovery Charge		-	11.3	-	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially Independent of Operating Temperature.

TYPICAL CHARACTERISTICS

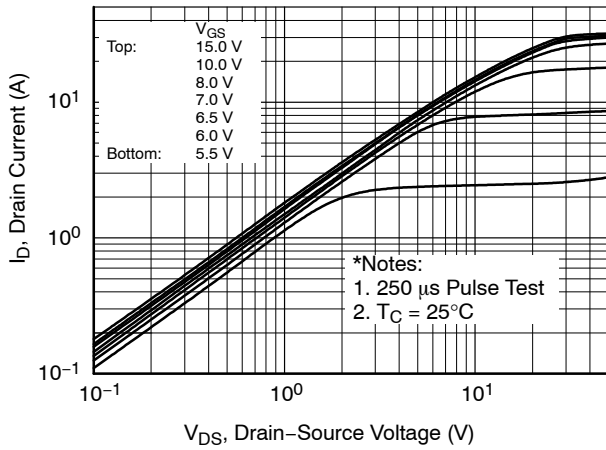


Figure 1. On-Region Characteristics

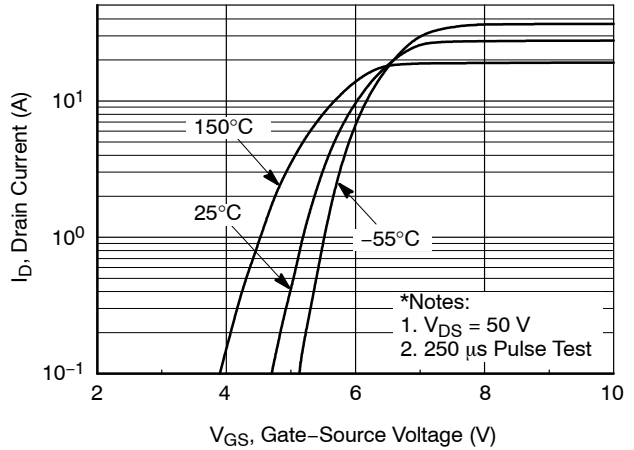


Figure 2. Transfer Characteristics

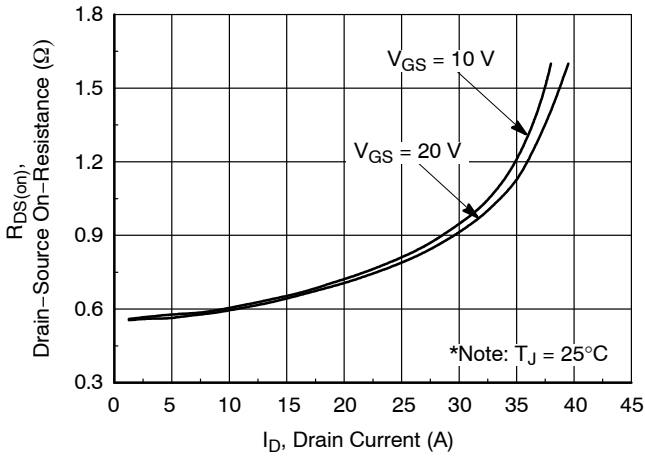


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

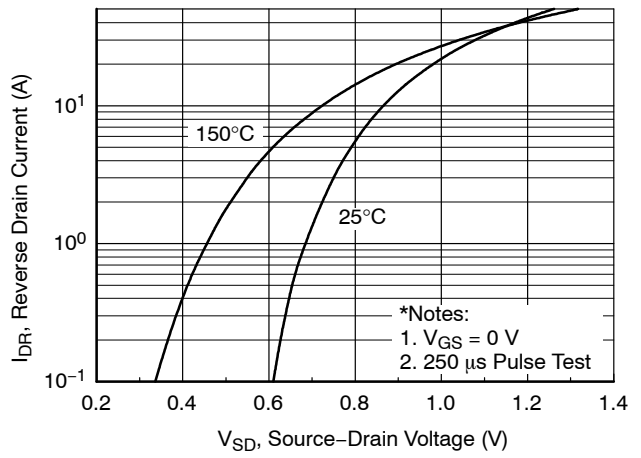


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

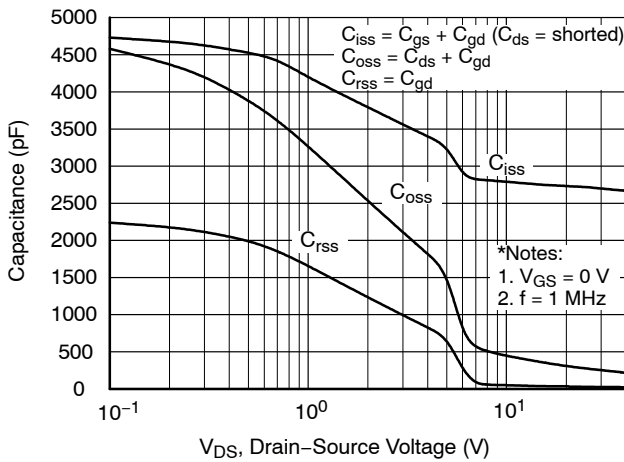


Figure 5. Capacitance Characteristics

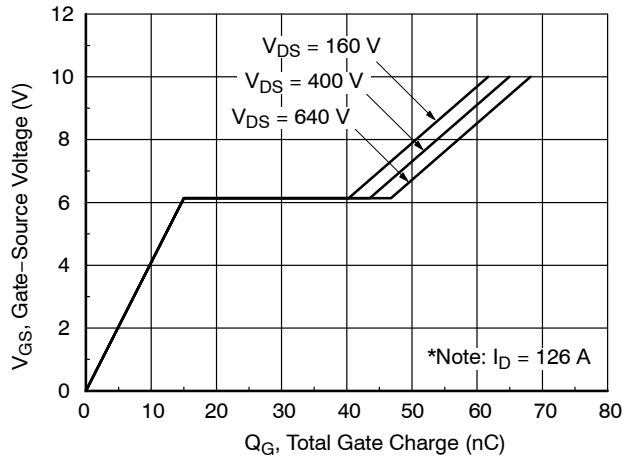


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

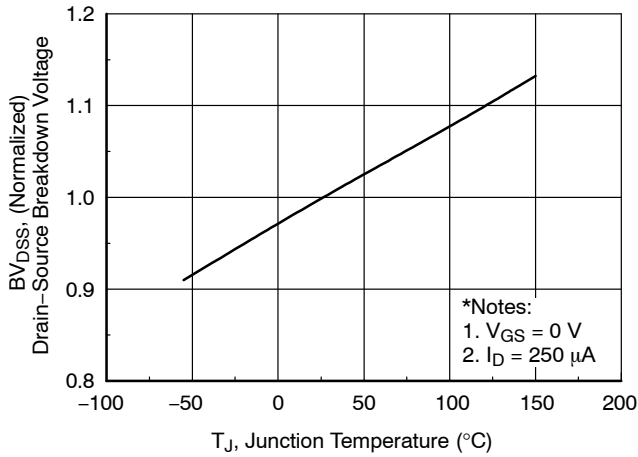


Figure 7. Breakdown Voltage Variation vs. Temperature

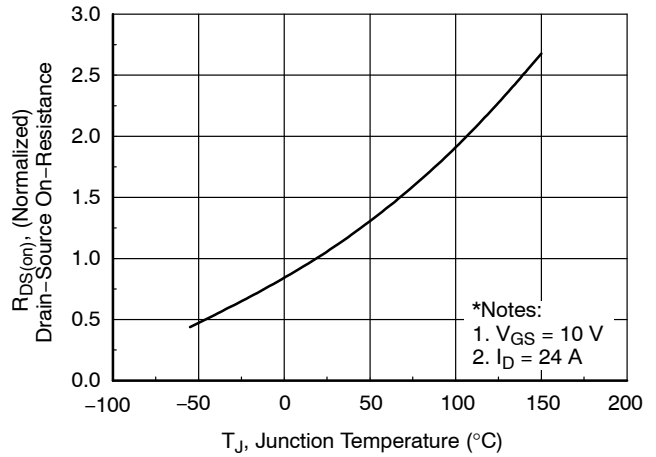


Figure 8. On-Resistance Variation vs. Temperature

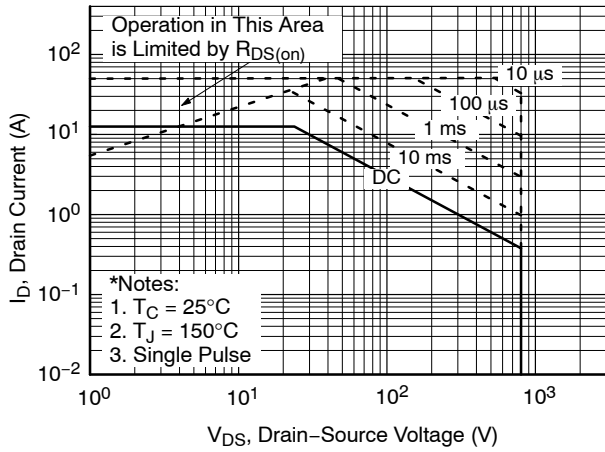


Figure 9. Maximum Safe Operating Area

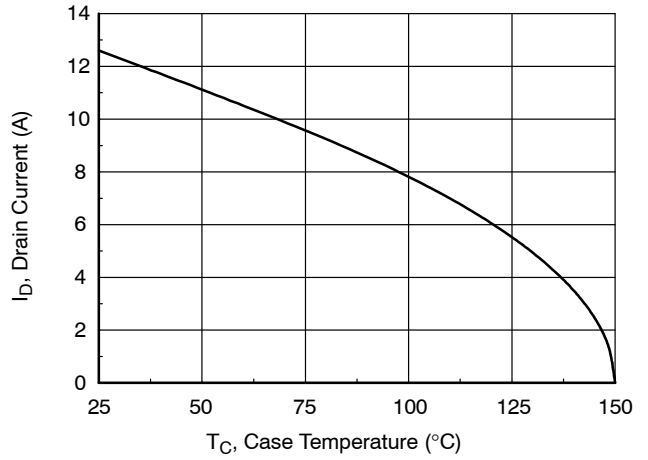


Figure 10. Maximum Drain Current vs. Case Temperature

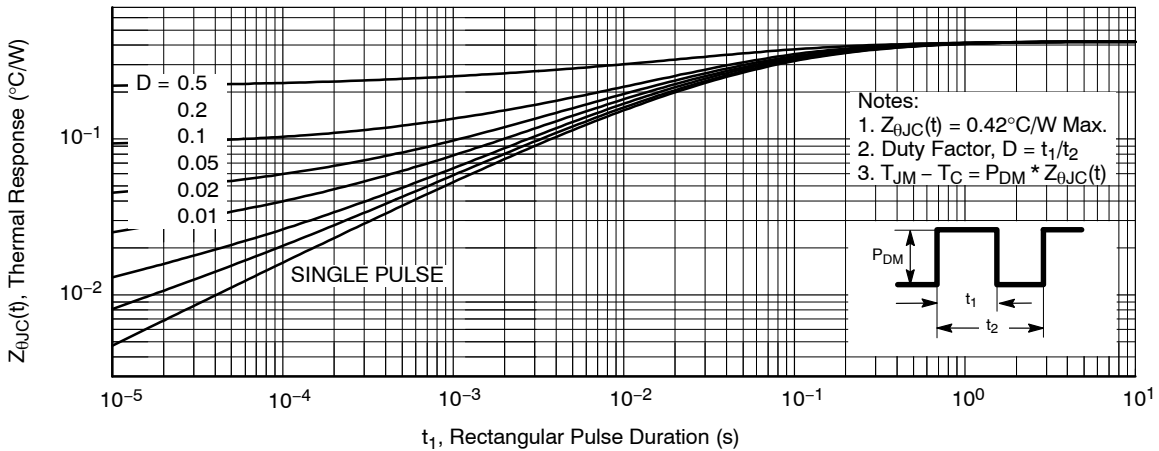


Figure 11. Transient Thermal Response Curve

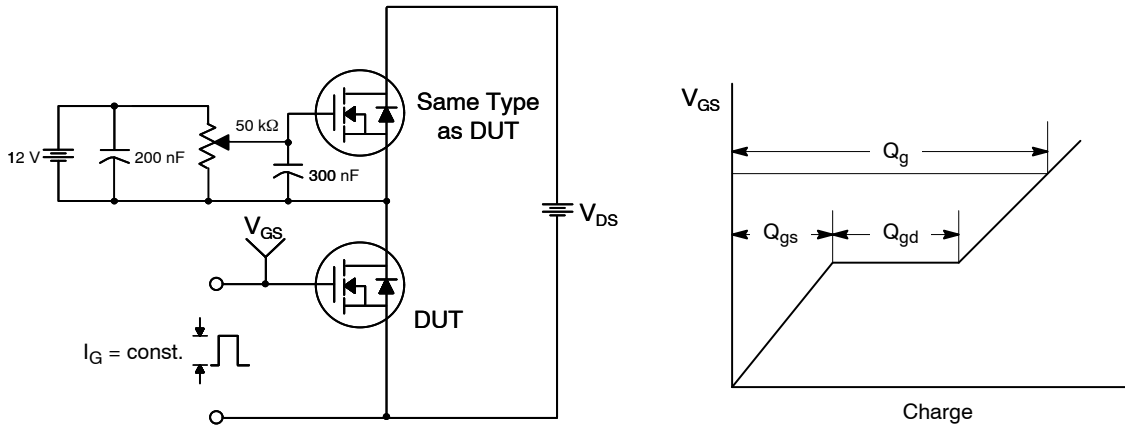


Figure 12. Gate Charge Test Circuit & Waveform

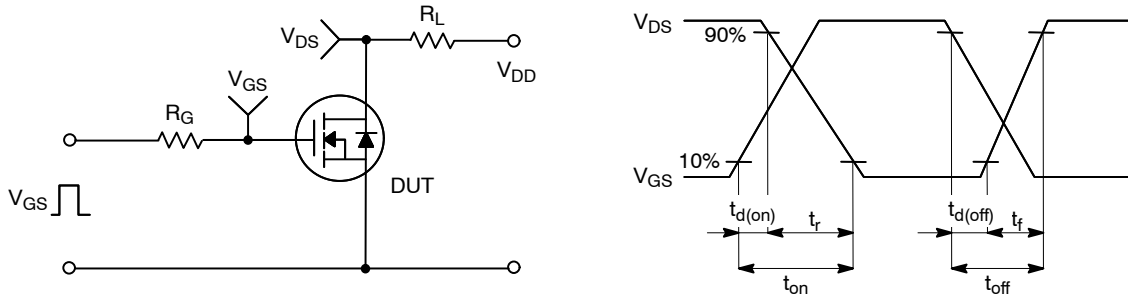


Figure 13. Resistive Switching Test Circuit & Waveforms

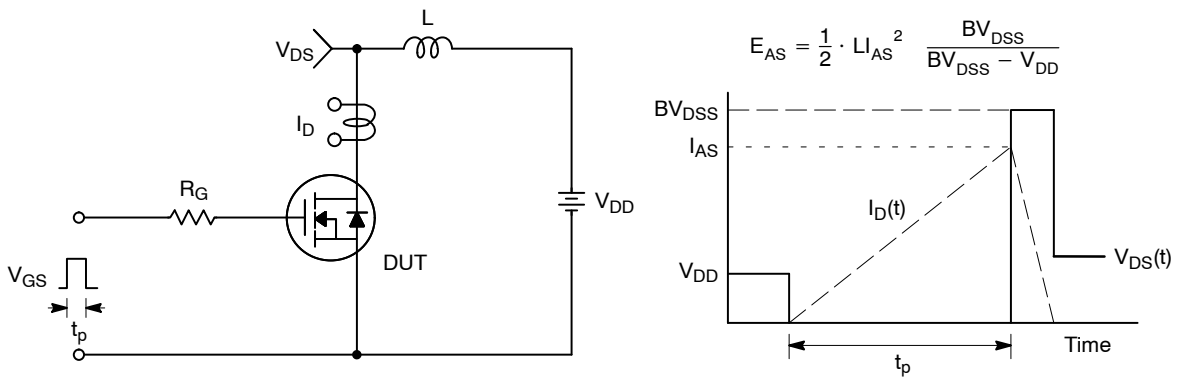


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

FQA13N80-F109

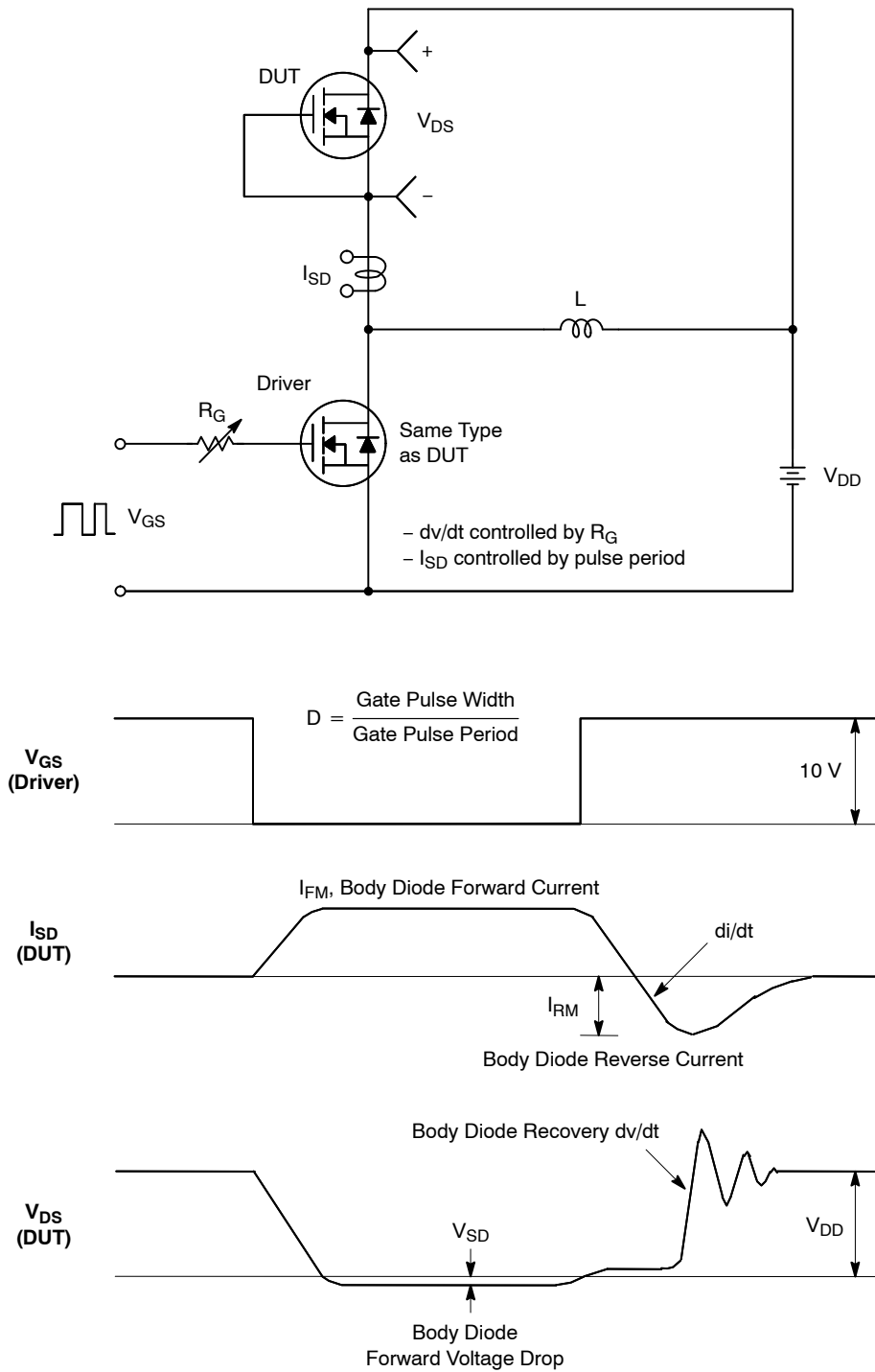


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

PACKAGE MARKING AND ORDERING INFORMATION

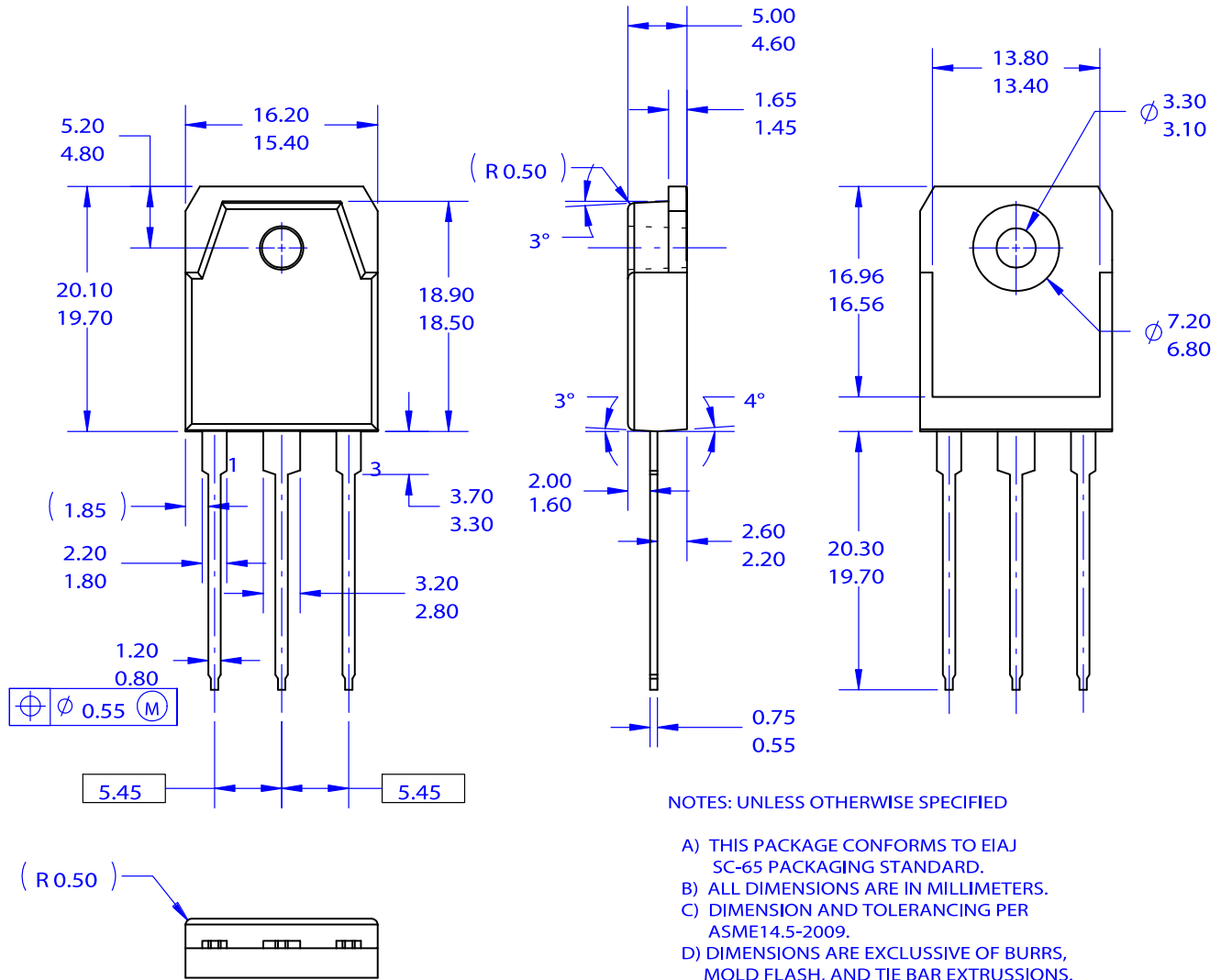
Part Number	Top Mark	Package	Package Method	Reel Size	Tape Width	Quantity
FQA13N80-F109	FQA13N80	TO-3P-3LD	Tube	N/A	N/A	450 Units /Tube

MECHANICAL CASE OUTLINE


PACKAGE DIMENSIONS

TO-3P-3LD / EIAJ SC-65, ISOLATED CASE 340BZ ISSUE O

DATE 31 OCT 2016



DOCUMENT NUMBER:	98AON13862G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-3P-3LD / EIAJ SC-65, ISOLATED	PAGE 1 OF 1

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales